RGC80TSX8R

1800V 40A Field Stop Trench IGBT

Datasheet

V _{CES}	1800V
I _{C (100°C)}	40A
V _{CE(sat) (Typ.)}	2.2V
P_D	535W

Outline TO-247N (1)(2)(3)

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Monolithic Body Diode

with Low Forward Voltage

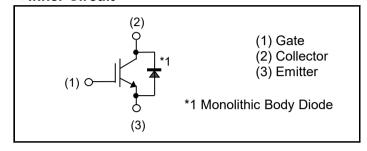
5) Pb - free Lead Plating; RoHS Compliant

Application

Voltage - resonance Inverter

ΙH

●Inner Circuit



Packaging Specifications

or dokaging opcomodations						
	Packaging	Tube				
	Reel Size (mm) Tape Width (mm)	-				
Tuno		-				
Туре	Basic Ordering Unit (pcs)	450				
	Packing Code	C11				
	Marking	RGC80TSX8R				

● **Absolute Maximum Ratings** (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V_{CES}	1800	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	80	Α
Collector Current	T _C = 100°C	I _C	40	Α
Pulsed Collector Current		I _{CP} *1	120	Α
Diode Forward Current	T _C = 25°C	I _F	80	Α
	T _C = 100°C	I _F	40	Α
Diode Pulsed Forward Current	•	I _{FP} *1	80	Α
Dower Dissipation	T _C = 25°C	P _D	535	W
Power Dissipation	T _C = 100°C	P _D	267	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax.}

●Thermal Resistance

Parameter	Cumbal	Values			Unit
Falametei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.28	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	0.28	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
- Farametei	Symbol	Conditions	Min.	Тур.	Max.	OIIII
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	1800	-	-	V
Collector Cut - off Current	I _{CES}	V _{CE} = 1860V, V _{GE} = 0V	1	1	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	1	1	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 120.7 \text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_{C} = 40A, V_{GE} = 15V$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$	-	2.2 2.9	5.0 -	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Offic
Input Capacitance	C _{ies}	V _{CE} = 30V	-	9550	-	
Output Capacitance	C_oes	V _{GE} = 0V	-	115	-	pF
Reverse transfer Capacitance	C _{res}	f = 1MHz	-	102	-	
Total Gate Charge	Q_g	V _{CE} = 600V	-	468	-	
Gate - Emitter Charge	Q_ge	I _C = 40A	-	93	-	nC
Gate - Collector Charge	Q _{gc}	V _{GE} = 15V	-	155	-	
Turn - on Delay Time	t _{d(on)}	I_C = 40A, V_{CC} = 600V, V_{GE} = 15V, R_G = 10 Ω , T_j = 25°C Inductive Load * E_{on} include diode reverse recovery	-	80	-	ns
Rise Time	t _r		-	53	-	
Turn - off Delay Time	t _{d(off)}		-	565	-	
Fall Time	t _f		-	55	-	
Turn - on Switching Loss	E _{on}		-	1.85	-	m l
Turn - off Switching Loss	E _{off}		-	1.60	2.15	- mJ
Turn - on Delay Time	t _{d(on)}		-	68	-	
Rise Time	t _r	I_C = 40A, V_{CC} = 600V, V_{GE} = 15V, R_G = 10 Ω , T_j = 175°C Inductive Load	-	52	-	
Turn - off Delay Time	t _{d(off)}		-	670	-	ns
Fall Time	t _f		-	55	-	
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	1.95	-	m l
Turn - off Switching Loss	E_{off}		-	2.00		mJ

●FRD Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Unit		
			Min.	Тур.	Max.	Onit
		$I_F = 40A, V_{GE} = 0V$				
Diode Forward Voltage	V_{F}	T _j = 25°C	-	1.8	2.3	V
		T _j = 175°C	-	2.4	-	

• Electrical Characteristic Curves

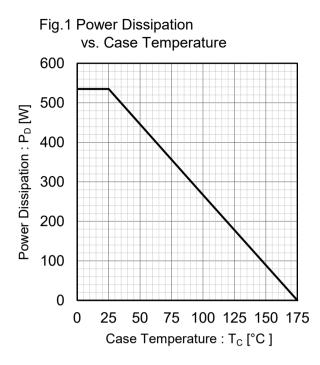


Fig.2 Collector Current vs. Case Temperature 90 80 70 Collector Current : Ic [A] 60 50 40 30 20 $T_j \le 175^{\circ}C$ $V_{GE} \ge 15V$ 10 0 25 50 75 100 125 150 175 Case Temperature : T_C [°C]

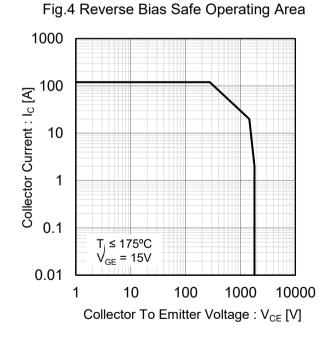
1000

Total 100

Tota

Collector To Emitter Voltage: V_{CE} [V]

Fig.3 Forward Bias Safe Operating Area



• Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

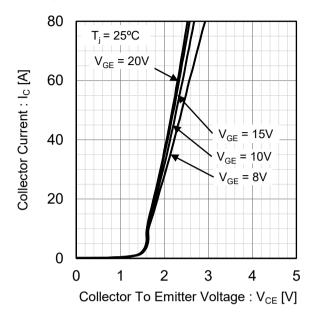


Fig.6 Typical Output Characteristics

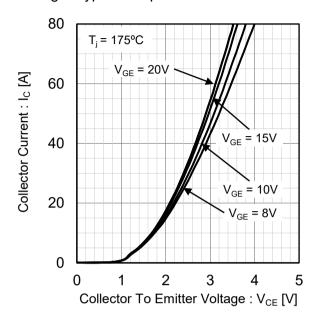


Fig.7 Typical Transfer Characteristics

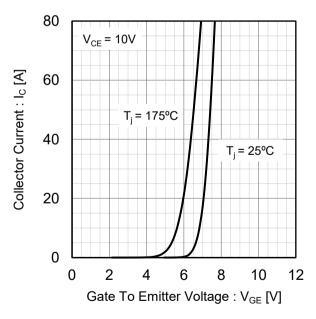
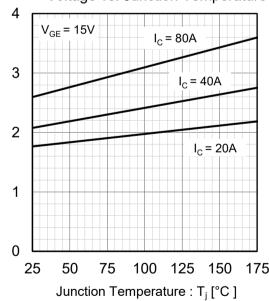


Fig.8 Typical Collector to Emitter Saturation Voltage vs. Junction Temperature



Collector To Emitter Saturation

Voltage: V_{CE(sat)} [V]



● Electrical Characteristic Curves

Fig.9 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

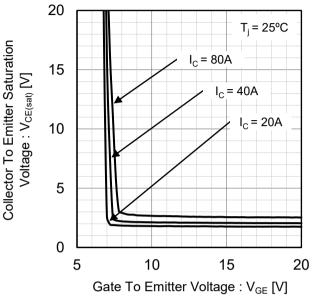


Fig.10 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

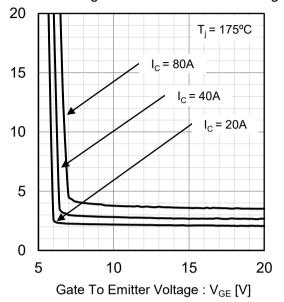


Fig.11 Typical Switching Time vs. Collector Current

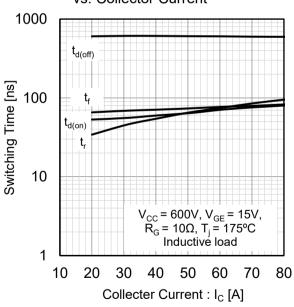
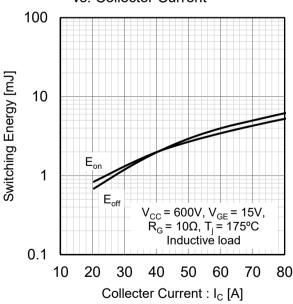


Fig.12 Typical Switching Energy Losses vs. Collector Current



Collector To Emitter Saturation

Voltage: V_{CE(sat)} [V]

•Electrical Characteristic Curves

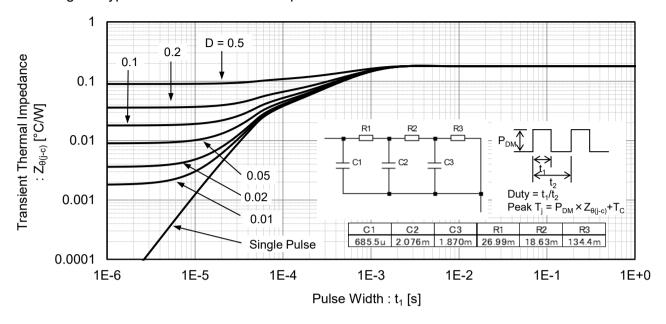
Fig.13 Typical Capacitance vs. Collector to Emitter Voltage 100000 C_{ies} 10000 Capacitance [pF] C_{oes} C_{res} 100 f = 1MHz $V_{GE} = 0V$ $T_j = 25^{\circ}C$ 10 0.01 0.1 1 10 100 Collector To Emitter Voltage: V_{CE} [V]

Fig.15 Typical Diode Forward Current vs. Forward Voltage 80 Forward Current : I_F [A] 60 $T_i = 25^{\circ}C$ T_i = 175°C 40 20 $V_{GE} = 0V$ 0 2 5 0 3 Forward Voltage: V_F [V]

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•Electrical Characteristic Curves

Fig.16 Typical Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

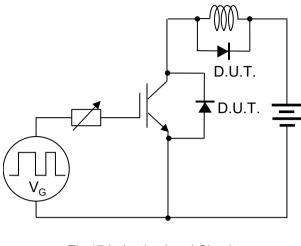


Fig.17 Inductive Load Circuit

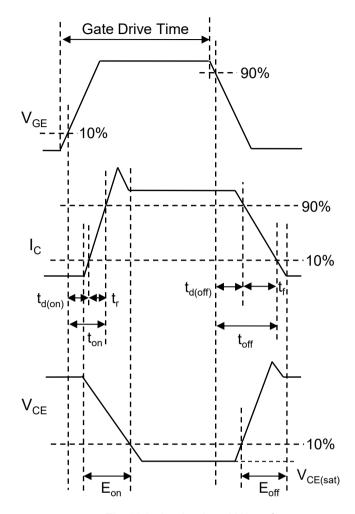


Fig.18 Inductive Load Waveform

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